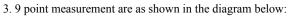
Icemos Technology Ltd Product Specification 1000.352902 Issue Date 20 December 2013 09

Category	Parameter 1.0 Diameter		Specification	Measurement Method
OverallWafer			100.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	569.00 +/- 11.00 μm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<3.00μm	
	7.0	Bow	<60.00μm	ADE to ASTM F534, 20%
	8.0	Warp	<60.00μm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	FZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	350.00 +/- 10.00 μm	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	>2000 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Polished with oxide and laser marking	Wafer Vendor
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle or Device Wafer	
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor
	22.0	Device Orientation	{111} +/- 1 degree. Off-orientation 2.5deg +/- 1deg	Wafer Vendor
	23.0	Nominal Thickness	218.00 +/- 1.00 μm	ADE, single point measurement
	24.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by process
	25.0	Device Doping Type	N	Wafer Vendor
	26.0	Device Dopant	As	Wafer Vendor
	27.0	Device Resistivity	<0.004 Ohmcm	Wafer Vendor
	28.0	Voids	none	Wafer Vendor
	29.0	Scratches	0	Bright Light, 100% (note 2)
	30.0	Haze	none	Bright Light, 100% (note 2)

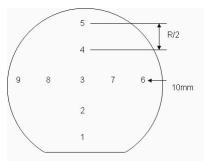
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Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box:	Max 25		
	Packaging:	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspec	etion performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall			

2. All bright light inspections performed exclude all water area outside the edge exclusion defined in Overal Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.



16/01/2019



Additional Information